

Technical Data Data Sheet N0063, Rev. A **Green Products**

246NQ200-1 SCHOTTKY RECTIFIER

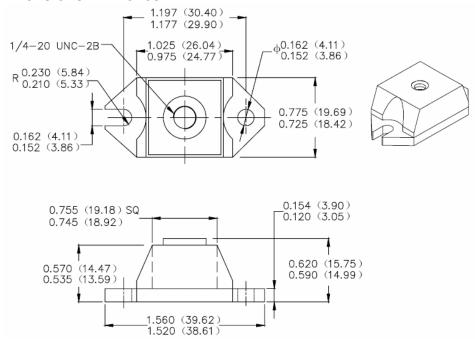
Applications:

• Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection

Features:

- 175 [°]C T_J operation
- Unique high power, Half-Pak module
- Low profile, high current package
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



PRM1-1(HALF PAK Module)

MARKING, MOLDING RESIN

Marking for 246NQ200-1, 1st row SS YYWWL, 2nd row 246NQ200-1 Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin

Epoxy resin UL:94V-0

[•] Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 🗏 (86) 25-87123907 •

[•] FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •



Technical Data Data Sheet N0063, Rev. A Green Products

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units_
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =110°C, rectangular wave form	240	Α
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	3950	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 240A, Pulse, T _J = 25 °C	1.12	V
	V_{F2}	@ 240A, Pulse, T _J = 125 °C	0.79	٧
Max. Reverse Current (per leg) *	I _{R1}	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	6	mA
	I_{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	85	mA
Max. Junction Capacitance (per leg)	C_{T}	$@V_R = 5V, T_C = 25 ^{\circ}C$ $f_{SIG} = 1MHz$	3600	pF
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	6.0	nΗ
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

^{*} Pulse Width < 300µs, Duty Cycle <2%

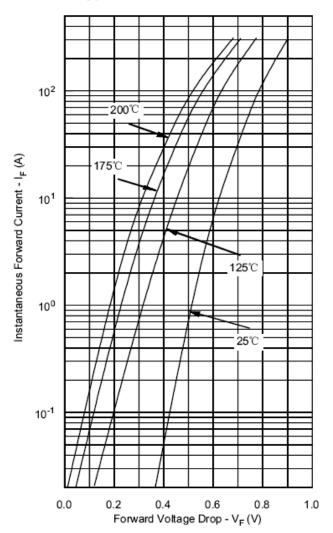
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifi	Units		
Max. Junction Temperature	TJ	-	-55 to +175		°C	
Max. Storage Temperature	T _{stg}	-	-55 to +175		°C	
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.20		°C/W	
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.15		°C/W	
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm	
Approximate Weight	wt	-	25.6		g	
Case Style	PRM1-1					

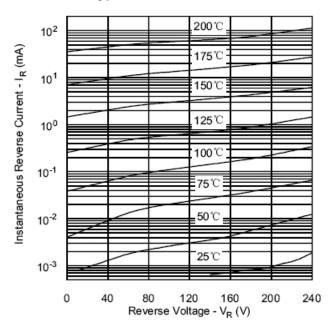


Technical Data Data Sheet N0063, Rev. A **Green Products**

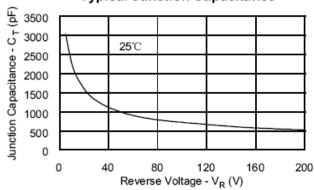
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



[•] Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 🗏 (86) 25-87123907 •

[•] FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •



246NQ200-1

Technical Data Data Sheet N0063, Rev. A **Green Products**

DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the SMC Sangdest Microelectronics (Nanjing) Co., Ltd sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall SMC Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). SMC Sangdest Microelectronics (Nanjing) Co., Ltd assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall SMC Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or SMC Sangdest Microelectronics (Nanjing) Co., Ltd.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of SMC Sangdest Microelectronics (Nanjing) Co., Ltd.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations..

[•] FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •